

PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT	
NATURE OF CONVEYANCE:	ASSIGNMENT	
SEQUENCE:	1	
CONVEYING PARTY DATA		
	Name	Execution Date
	FUJI ELECTRIC CO., LTD.	11/17/2014
RECEIVING PARTY DATA		
Name:	INTELLECTUALS HIGH-TECH KFT.	
Street Address:	ARPAD UT 48-50	
Internal Address:	I/5	
City:	BUDAPEST	
State/Country:	HUNGARY	
Postal Code:	1042	
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Property Type	Number	
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NAME OF SUBMITTER:	ANDREW B. KARP	
SIGNATURE:	/Andrew B. Karp/	
DATE SIGNED:	12/09/2016	
Total Attachments: 12		
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ASSIGNMENT OF PATENT RIGHTS

For good and valuable consideration, the receipt of which is hereby acknowledged, Fuji Electric Co., Ltd., a Japanese corporation having its registered address at 1-1, Tanabeshinden, Kawasaki-ku, Kawasaki-shi, Kanagawa 210-9530, Japan ("**Assignor**"), does hereby sell, assign, transfer, and convey unto Intellectuals High-Tech Kft., an Hungarian limited liability company, having an address at Budapest 1042, Arpad ut 48-50. I/5. Hungary ("**Assignee**"), or its designees, all right, title, and interest that exist today and may exist in the future in and to any and all of the following (collectively, the "**Patent Rights**"):

(a) the provisional patent applications, patent applications and patents listed in the table below (the "**Patents**");

<u>Patent or application no.</u>	<u>Country</u>	<u>Filing Date</u>	<u>Title of Patent and First Named Inventors</u>
JP5062538	JP	08/28/2008	Magnetic Memory Element, Method For Driving The Magnetic Memory Element, And Nonvolatile Storage Device Yasushi Ogimoto
KR10-1397654	KR	08/28/2008	Magnetic Memory Element, Method For Driving The Magnetic Memory Element, And Nonvolatile Storage Device Yasushi Ogimoto
8279661	US	08/28/2008	Magnetic Memory Element, Driving Method For The Same, And Nonvolatile Storage Device Yasushi Ogimoto
EP08862686.6	EP	08/28/2008	Magnetic Memory Element, Method For Driving The Magnetic Memory Element, And Nonvolatile Storage Device Yasushi Ogimoto
DE602009026495.8	DE	07/08/2009	Magnetic Memory Element And Storage Device Using Same Michiya Yamada

FR2333826	FR	7/8/2009	Magnetic Memory Element And Storage Device Using Same Michiya Yamada
8803263	US	07/08/2009	Magnetic Memory Element And Storage Device Using The Same Michiya Yamada
KR10-2011-7005673	KR	07/08/2009	Magnetic Memory Element And Storage Device Using Same Michiya Yamada
JP2013-170692	JP	08/20/2013	Storage Device Using The Same, And Magnetic Memory Element Michiya Yamada
14/250461	US	04/11/2014	MAGNETIC MEMORY ELEMENT AND STORAGE DEVICE USING THE SAME Michiya Yamada
DE602008032309.9	DE	09/05/2008	Spin Valve Element And Its Driving Method And Storage Device Employing Them Haruo Kawakami
FR2320489	FR	09/05/2008	Spin Valve Element And Its Driving Method And Storage Device Employing Them Haruo Kawakami
8654576	US	09/05/2008	Spin Valve Element, Method Of Driving The Same, And Storage Device Using The Same Haruo Kawakami

JP5354389	JP	09/05/2008	Spin Valve Element And Its Driving Method And Storage Device Employing Them Haruo Kawakami
KR10-2010-7023542	KR	09/05/2008	Spin Valve Element And Its Driving Method And Storage Device Employing Them Haruo Kawakami
EP08872063.6	EP	08/28/2008	Magnetic Memory Element, Method For Driving Same, And Nonvolatile Storage Yasushi Ogimoto
8274820	US	08/28/2008	Magnetic Memory Element, Method Of Driving Same, And Nonvolatile Storage Device Yasushi Ogimoto
JP5057254	JP	08/28/2008	Magnetic Memory Element, Method For Driving Same, And Nonvolatile Storage Yasushi Ogimoto
KR10-2010-7012211	KR	08/28/2008	Magnetic Memory Element, Method For Driving Same, And Nonvolatile Storage Yasushi Ogimoto
JP5534408	JP	08/28/2008	Spin-Valve Element Driving Method, And Spin-Valve Element Haruo Kawakami
7924609	US	08/28/2008	Spin Valve Element Driving Method And Spin Valve Element Haruo Kawakami

KR10-1291778	KR	08/28/2008	Spin-Valve Element Driving Method, And Spin-Valve Element Haruo Kawakami
EP08863154.4	EP	08/28/2008	Spin-Valve Element Driving Method, And Spin-Valve Element Haruo Kawakami
12/673935 Fuji did not reply to office action dated Jun 30, 2014.	US	08/28/2008	Ferromagnetic Tunnel Junction Element And Method Of Driving Ferromagnetic Tunnel Junction Element Takuya Ono
14/522594	US	10/24/2014	Spin Valve Element Haruo Kawakami
JP5440509	JP	10/02/2009	Magnetoresistive Element And Memory Device Using Same Michiya Yamada
DE602009026652.7	DE	10/02/2009	Magnetoresistive Element And Memory Device Using Same Michiya Yamada
FR2375464	FR	10/02/2009	Magnetoresistive Element And Memory Device Using Same Michiya Yamada
KR10-2011-7013958 (KR10-1458263)	KR	10/02/2009	Magnetoresistive Element And Memory Device Using Same Michiya Yamada
8456896	US	06/21/2011	Magnetoresistance Element And Storage Device Using The Same Michiya Yamada

JP2013-112009	JP	05/28/2013	Memory Device Using The Same Magnetic And Resistive Element Michiya Yamada
7626856	US	03/07/2007	Magnetic Recording Element Takuya Ono
JP5092464	JP	03/13/2007	Magnetic Wall Displacement Type Magnetic Recording Element With Magnetic Wall Displacement Detecting Terminals Takuya Ono
8174870	US	09/11/2009	Magnetic Recording Element Takuya Ono
8432728	US	09/19/2011	Magnetic Recording Element Takuya Ono
8679653	US	09/05/2008	Spin-Valve Recording Element And Storage Device Haruo Kawakami
DE602008034121.6	DE	09/05/2008	Spin Valve Recording Element And Storage Device Haruo Kawakami
FR2306540	FR	09/05/2008	Spin Valve Recording Element And Storage Device Haruo Kawakami
JP5354388	JP	09/05/2008	Spin Valve Recording Element And Storage Device Haruo Kawakami
KR10-2010-7026126	KR	09/05/2008	Spin Valve Element And Storage Device Haruo Kawakami

8514617	US	03/17/2010	Magnetic Memory Element And Storage Device Using The Same Michiya Yamada: Yasushi Ogimoto
JP5435026	JP	03/17/2010	Magnetic Memory Element And Storage Device Using Same Michiya Yamada
KR10-2011-7022001	KR	03/17/2010	Magnetic Memory Element And Storage Device Using Same Michiya Yamada
EP10777613.0	EP	03/17/2010	Magnetic Memory Element And Storage Device Using Same Michiya Yamada
KR10-2010-7008724 (KR10-1456950)	KR	08/28/2008	Spin Valve Element, And Its Driving Method Haruo Kawakami
8411395	US	08/28/2008	Spin Valve Element And Method Of Driving Same Haruo Kawakami
EP08842281.1	EP	08/28/2008	Spin Valve Element, And Its Driving Method Haruo Kawakami
JP5495108	JP	08/28/2008	Spin-Valve Element And Its Manufacturing Method Haruo Kawakami
12/739741	US	08/28/2008	Spin Valve Element And Method Of Manufacturing Same Haruo Kawakami

EP08841627.6	EP	08/28/2008	Spin-Valve Element And Its Manufacturing Method Haruo Kawakami
KR10-2010-7007998	KR	08/28/2008	Spin-Valve Element And Its Manufacturing Method Haruo Kawakami
8750028	US	05/14/2010	Magnetic Memory Element And Driving Method For Same Yasushi Ogimoto
JP5321991	JP	05/14/2010	Magnetic Memory Element And Driving Method Therefor Yasushi Ogimoto
KR10-2011-7017318	KR	05/14/2010	Magnetic Memory Element And Driving Method Therefor Yasushi Ogimoto
DE602010019862.6	DE	05/14/2010	Magnetic Memory Element And Driving Method Therefor Yasushi Ogimoto
FR2385548	FR	05/14/2010	Magnetic Memory Element And Driving Method Therefor Yasushi Ogimoto
13/387318	US	04/12/2010	Non-Contact Current Sensor Yasushi Ogimoto
EP10804161.7	EP	04/12/2010	Non-Contact Current Sensor Yasushi Ogimoto
JP5403056	JP	04/12/2010	Non-Contact Current Sensor Yasushi Ogimoto

KR10-2012-7002155	KR	04/12/2010	Non-Contact Current Sensor Yasushi Ogimoto
JP2011-531848 (JP5578448)	JP	08/04/2010	Magnetoresistive Element And Non-Volatile Semiconductor Memory Device Using Same Michiya Yamada
13/395437	US	08/04/2010	Magnetoresistance Element And Non-Volatile Semiconductor Storage Device Using Same Magnetoresistance Element Michiya Yamada
KR10-2012-7006109	KR	08/04/2010	Magnetoresistive Element And Non-Volatile Semiconductor Memory Device Using Same Michiya Yamada
EP10816986.3	EP	08/04/2010	Magnetoresistive Element And Non-Volatile Semiconductor Memory Device Using Same Michiya Yamada
EP09830245.8	EP	08/25/2009	Magnetic Memory Element And Nonvolatile Storage Device Yasushi Ogimoto
13/131103	US	08/25/2009	Magnetic Memory Element And Non-Volatile Storage Device Yasushi Ogimoto
JP5316967	JP	08/25/2009	Magnetic Memory Element And Nonvolatile Storage Device Yasushi Ogimoto
KR10-2011-7011820	KR	08/25/2009	Magnetic Memory Element And Nonvolatile Storage Device Yasushi Ogimoto

JP5387990	JP	09/05/2008	Magnetic Memory Element And Its Driving Method And Nonvolatile Memory Device Yasushi Ogimoto
KR10-2010-7028481	KR	09/05/2008	Magnetic Memory Element And Its Driving Method And Nonvolatile Memory Device Yasushi Ogimoto
DE602008021906.2	DE	09/05/2008	Magnetic Memory Element And Its Driving Method And Nonvolatile Memory Device Haruo Kawakami
8709617	US	09/05/2008	Magnetic Memory Element, Driving Method For Same, And Nonvolatile Storage Device Yasushi Ogimoto
FR2306510	FR	09/05/2008	Magnetic Memory Element And Its Driving Method And Nonvolatile Memory Device Yasushi Ogimoto

(b) all patents and patent applications (i) to which any of the Patents directly or indirectly claims priority, and/or (ii) for which any of the Patents directly or indirectly forms a basis for priority;

(c) all reissues, reexaminations, extensions, continuations, continuations in part, continuing prosecution applications, requests for continuing examinations, divisions, registrations of any item in any of the foregoing categories (a) and (b);

(d) all foreign patents, patent applications, and counterparts relating to any item in any of the foregoing categories (a) through (c), including, without limitation, certificates of invention, utility models, industrial design protection, design patent protection, and other governmental grants or issuances;

(e) all items in any of the foregoing in categories (b) through (d), whether or not expressly listed as Patents above and whether or not claims in any of the foregoing have been rejected, withdrawn, cancelled, or the like;

(f) inventions, invention disclosures, and discoveries described in any of the Patents and/or any item in the foregoing categories (b) through (e) that (i) are included in any claim in the Patents and/or any item in the foregoing categories (b) through (e), (ii) are subject matter capable of being reduced to a patent claim in a reissue or reexamination proceeding brought on any of the Patents and/or any item in the foregoing categories (b) through (e), and/or (iii) could have been included as a claim in any of the Patents and/or any item in the foregoing categories (b) through (e);

(g) all rights to apply in any or all countries of the world for patents, certificates of invention, utility models, industrial design protections, design patent protections, or other governmental grants or issuances of any type related to any item in any of the foregoing categories (a) through (f), including, without limitation, under the Paris Convention for the Protection of Industrial Property, the International Patent Cooperation Treaty, or any other convention, treaty, agreement, or understanding;

(h) all causes of action (whether known or unknown or whether currently pending, filed, or otherwise) and other enforcement rights under, or on account of, any of the Patents and/or any item in any of the foregoing categories (b) through (g), including, without limitation, all causes of action and other enforcement rights for

- (1) damages,
- (2) injunctive relief, and
- (3) any other remedies of any kind

for past, current, and future infringement; and

(i) all rights to collect royalties and other payments under or on account of any of the Patents and/or any item in any of the foregoing categories (b) through (h).

Assignor represents, warrants and covenants that:

(1) Assignor has the full power and authority, and has obtained all third party consents, approvals and/or other authorizations required to enter into this Agreement and to carry out its obligations hereunder, including the assignment of the Patent Rights to Assignee; and

(2) Assignor owns, and by this document assigns to Assignee, all right, title, and interest to the Patent Rights, including, without limitation, all right, title, and interest to sue for infringement of the Patent Rights. Assignor has obtained and properly recorded previously executed assignments for the Patent Rights as necessary to fully perfect its rights and title therein in accordance with governing law and regulations in each respective

jurisdiction. The Patent Rights are free and clear of all liens, claims, mortgages, security interests or other encumbrances, and restrictions. There are no actions, suits, investigations, claims or proceedings threatened, pending or in progress relating in any way to the Patent Rights. There are no existing contracts, agreements, options, commitments, proposals, bids, offers, or rights with, to, or in any person to acquire any of the Patent Rights.

Assignor hereby authorizes the respective patent office or governmental agency in each jurisdiction to issue any and all patents, certificates of invention, utility models or other governmental grants or issuances that may be granted upon any of the Patent Rights in the name of Assignee, as the assignee to the entire interest therein.

Assignor will, at the reasonable request of Assignee, do all things necessary, proper, or advisable, including without limitation, the execution, acknowledgment, and recordation of specific assignments, oaths, declarations, and other documents on a country-by-country basis, to assist Assignee in obtaining, perfecting, sustaining, and/or enforcing the Patent Rights.

The terms and conditions of this Assignment of Patent Rights will inure to the benefit of Assignee, its successors, assigns, and other legal representatives and will be binding upon Assignor, its successors, assigns, and other legal representatives.

IN WITNESS WHEREOF this Assignment of Patent Rights is executed at Tokyo
_____ on November 17, 2014.

ASSIGNOR:

Fuji Electric Co., Ltd.

By: Masaharu Sinobe

Name: Masaharu Sinobe

Title: General Manager, Intellectual Property Center

(Signature *MUST* be attested)

ATTESTATION OF SIGNATURE PURSUANT TO 28 U.S.C. § 1746

The undersigned witnessed the signature of Masaharu Sinobe to the above Assignment of Patent Rights on behalf of Fuji Electric Co., Ltd. and makes the following statements:

1. I am over the age of 18 and competent to testify as to the facts in this Attestation block if called upon to do so.

2. Masaharu Sinobe is personally known to me (or proved to me on the basis of satisfactory evidence) and appeared before me on November 17, 2014 to execute the above Assignment of Patent Rights on behalf of Fuji Electric Co., Ltd..

3. Masaharu Sinobe subscribed to the above Assignment of Patent Rights on behalf of Fuji Electric Co., Ltd..

I declare under penalty of perjury under the laws of the United States of America that the statements made in the three (3) numbered paragraphs immediately above are true and correct.

EXECUTED on 2014-11-17(date)

Yoichi Matsumoto

Print Name: Yoichi Matumoto